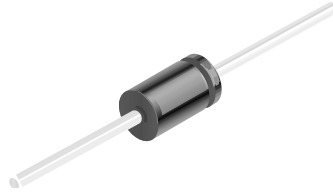


# BAV19 / 20 / 21



**DO-35**

Color Band Denotes Cathode

## Small Signal Diode

### Absolute Maximum Ratings\*

$T_A = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Value	Units
$V_{RRM}$	Maximum Repetitive Reverse Voltage	<b>BAV19</b>	120 V
		<b>BAV20</b>	200 V
		<b>BAV21</b>	250 V
$I_{F(AV)}$	Average Rectified Forward Current	200	mA
$I_{FSM}$	Non-repetitive Peak Forward Surge Current Pulse Width = 1.0 second Pulse Width = 1.0 microsecond	1.0	A
		4.0	A
$T_{stg}$	Storage Temperature Range	-65 to +200	$^\circ\text{C}$
$T_J$	Operating Junction Temperature	175	$^\circ\text{C}$

\* These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

**NOTES:**

- 1) These ratings are based on a maximum junction temperature of 200 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

### Thermal Characteristics

Symbol	Parameter	Value	Units
$P_D$	Power Dissipation	500	mW
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	300	$^\circ\text{C}/\text{W}$

### Electrical Characteristics

$T_A = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
$V_R$	Breakdown Voltage	<b>BAV19</b> $I_R = 100 \mu\text{A}$	120		V
		<b>BAV20</b> $I_R = 100 \mu\text{A}$	200		V
		<b>BAV21</b> $I_R = 100 \mu\text{A}$	250		V
$V_F$	Forward Voltage	$I_F = 100 \text{ mA}$		1.0	V
		$I_F = 200 \text{ mA}$		1.25	V
$I_R$	Reverse Current	$V_R = 100 \text{ V}$		100	nA
		<b>BAV19</b> $V_R = 100 \text{ V}, T_A = 150^\circ\text{C}$		100	$\mu\text{A}$
		$V_R = 150 \text{ V}$		100	nA
		<b>BAV20</b> $V_R = 150 \text{ V}, T_A = 150^\circ\text{C}$		100	$\mu\text{A}$
		$V_R = 200 \text{ V}$		100	nA
<b>BAV21</b>		$V_R = 200 \text{ V}, T_A = 150^\circ\text{C}$		100	$\mu\text{A}$
$C_T$	Total Capacitance	$V_R = 0, f = 1.0 \text{ MHz}$		5.0	pF
$t_{rr}$	Reverse Recovery Time	$I_F = I_R = 30 \text{ mA}, I_{RR} = 3.0 \text{ mA}, R_L = 100\Omega$		50	ns

Typical Characteristics

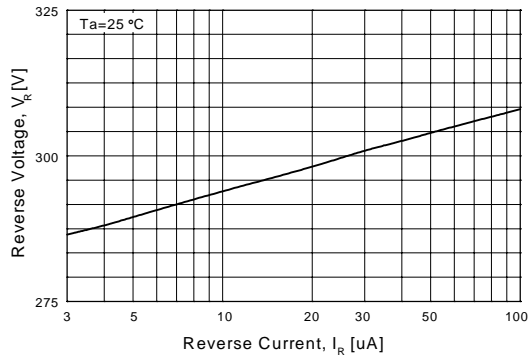


Figure 1. Reverse Voltage vs Reverse Current  
BV - 1.0 to 100uA

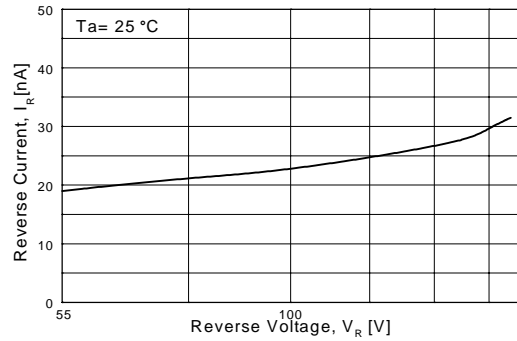


Figure 2. Reverse Current vs Reverse Voltage  
IR - 55 to 205 V  
GENERAL RULE: The Reverse Current of a diode will approximately double for every ten (10) Degree C increase in Temperature

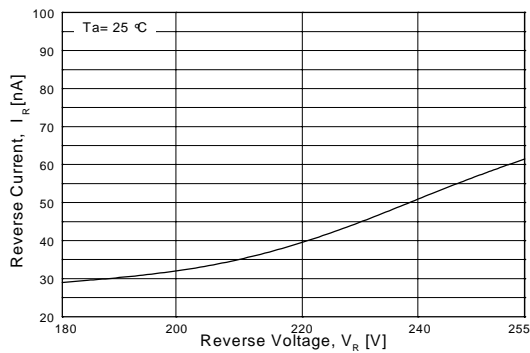


Figure 3. Reverse Current vs Reverse Voltage  
IR - 180 to 225 V  
GENERAL RULE: The Reverse Current of a diode will approximately double for every ten (10) Degree C increase in Temperature

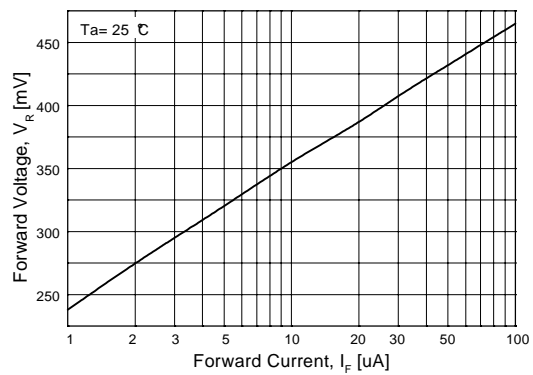


Figure 4. Forward Voltage vs Forward Current  
VF - 1.0 to 100uA

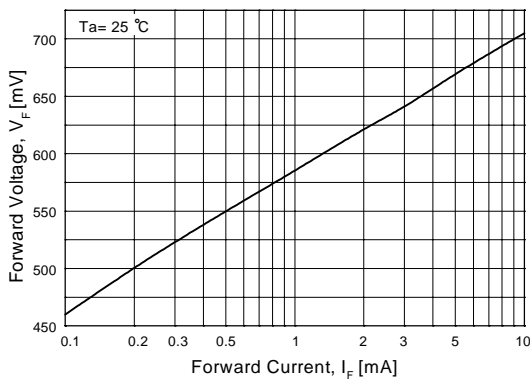


Figure 5. Forward Voltage vs Forward Current  
VF - 0.1 to 10mA

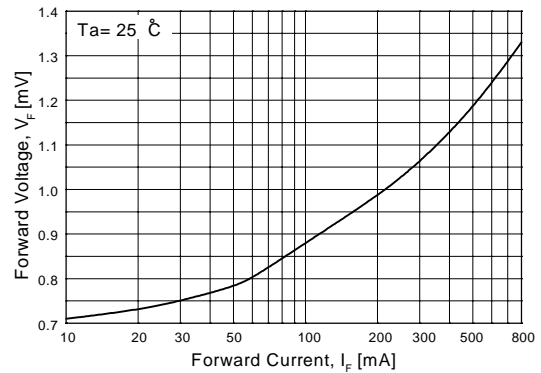


Figure 6. Forward Voltage vs Forward Current  
VF - 10 to 800mA

Typical Characteristics (continued)

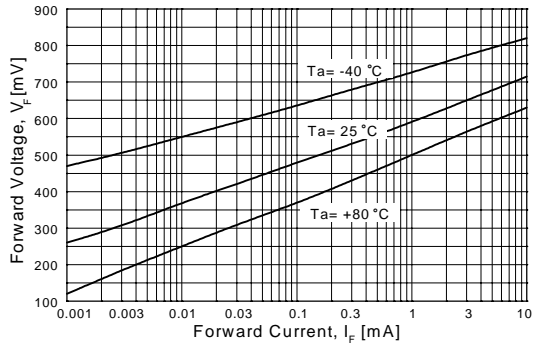


Figure 7. Forward Voltage vs Ambient Temperature  
VF - 1.0 uA - 10 mA (-40 to +80 Deg C)

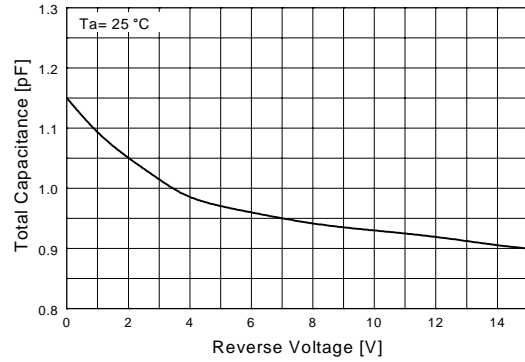


Figure 8. Total Capacitance

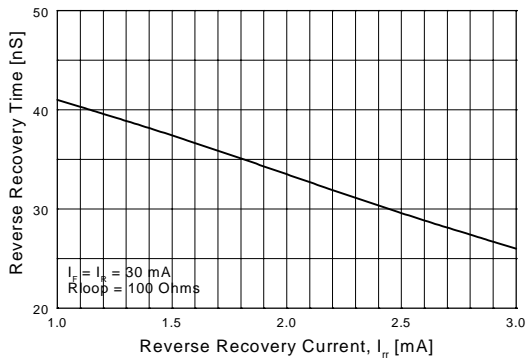


Figure 9. Reverse Recovery Time vs Reverse Recovery Current

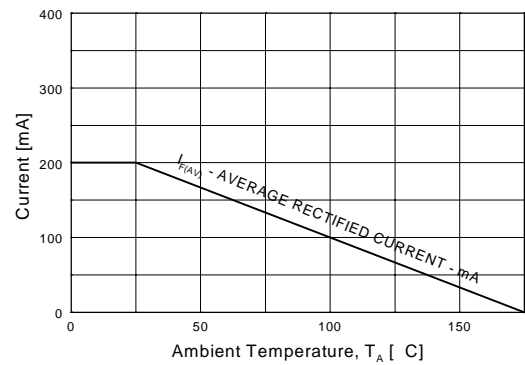


Figure 10. Average Rectified Current ( $I_{F(AV)}$ ) versus Ambient Temperature ( $T_A$ )

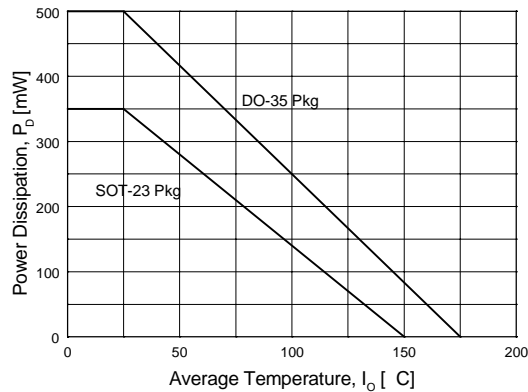


Figure 11. Power Derating Curve

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